



ABSTRACT

There is provided a semiconductor device comprising: a first plating layer (30) formed on one surface of an interconnect pattern (21); a second plating layer (32) formed within through holes (28) in the interconnect pattern (21); a semiconductor chip (10) electrically connected to the first plating layer (30); an anisotropic conductive material (34) provided on the first plating layer (30); and a conductive material (36) provided on the second plating layer (32), wherein the first plating layer (30) has appropriate adhesion properties with the anisotropic conductive material (34), and the second plating layer (32) has appropriate adhesion properties with the conductive material (36).